

MMBT6520L, NSVMMBT6520L

High Voltage Transistor

PNP Silicon



ON Semiconductor®

www.onsemi.com

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

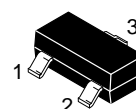
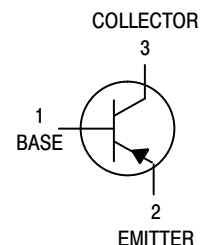
Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	–350	Vdc
Collector–Base Voltage	V_{CBO}	–350	Vdc
Emitter–Base Voltage	V_{EBO}	–5.0	Vdc
Base Current	I_B	–250	mA
Collector Current – Continuous	I_C	–500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

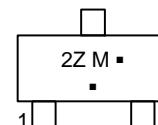
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR–5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



SOT–23 (TO–236)
CASE 318
STYLE 6

MARKING DIAGRAM



2Z = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT6520LT1G	SOT–23 (Pb–Free)	3000 / Tape & Reel
MMBT6520LT3G	SOT–23 (Pb–Free)	10,000 / Tape & Reel
NSVMMBT6520LT1G	SOT–23 (Pb–Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage ($I_C = -1.0\text{ mA}$)	$V_{(BR)CEO}$	-350	-	Vdc
Collector–Base Breakdown Voltage ($I_C = -100\ \mu\text{A}$)	$V_{(BR)CBO}$	-350	-	Vdc
Emitter–Base Breakdown Voltage ($I_E = -10\ \mu\text{A}$)	$V_{(BR)EBO}$	-5.0	-	Vdc
Collector Cutoff Current ($V_{CB} = -250\text{ V}$)	I_{CBO}	-	-50	nA
Emitter Cutoff Current ($V_{EB} = -4.0\text{ V}$)	I_{EBO}	-	-50	nA
ON CHARACTERISTICS				
DC Current Gain ($I_C = -1.0\text{ mA}$, $V_{CE} = -10\text{ V}$) ($I_C = -10\text{ mA}$, $V_{CE} = -10\text{ V}$) ($I_C = -30\text{ mA}$, $V_{CE} = -10\text{ V}$) ($I_C = -50\text{ mA}$, $V_{CE} = -10\text{ V}$) ($I_C = -100\text{ mA}$, $V_{CE} = -10\text{ V}$)	h_{FE}	20 30 30 20 15	- - 200 200 -	-
Collector–Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -1.0\text{ mA}$) ($I_C = -20\text{ mA}$, $I_B = -2.0\text{ mA}$) ($I_C = -30\text{ mA}$, $I_B = -3.0\text{ mA}$) ($I_C = -50\text{ mA}$, $I_B = -5.0\text{ mA}$)	$V_{CE(sat)}$	- - - -	-0.30 -0.35 -0.50 -1.0	Vdc
Base–Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -1.0\text{ mA}$) ($I_C = -20\text{ mA}$, $I_B = -2.0\text{ mA}$) ($I_C = -30\text{ mA}$, $I_B = -3.0\text{ mA}$)	$V_{BE(sat)}$	- - -	-0.75 -0.85 -0.90	Vdc
Base–Emitter On Voltage ($I_C = -100\text{ mA}$, $V_{CE} = -10\text{ V}$)	$V_{BE(on)}$	-	-2.0	Vdc
SMALL–SIGNAL CHARACTERISTICS				
Current–Gain – Bandwidth Product ($I_C = -10\text{ mA}$, $V_{CE} = -20\text{ V}$, $f = 20\text{ MHz}$)	f_T	40	200	MHz
Collector–Base Capacitance ($V_{CB} = -20\text{ V}$, $f = 1.0\text{ MHz}$)	C_{cb}	-	6.0	pF
Emitter–Base Capacitance ($V_{EB} = -0.5\text{ V}$, $f = 1.0\text{ MHz}$)	C_{eb}	-	100	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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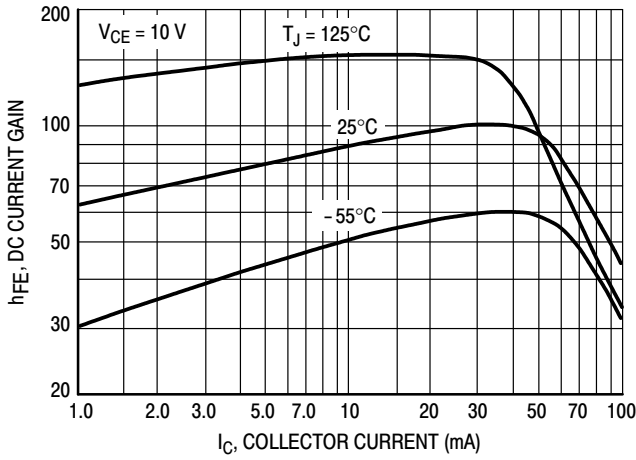


Figure 1. DC Current Gain

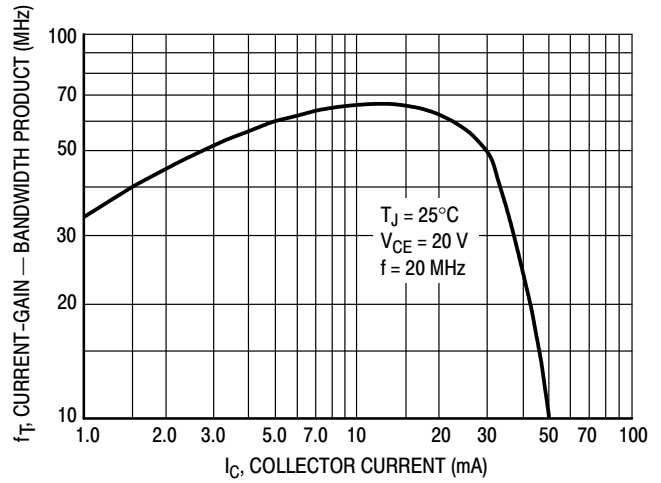


Figure 2. Current-Gain — Bandwidth Product

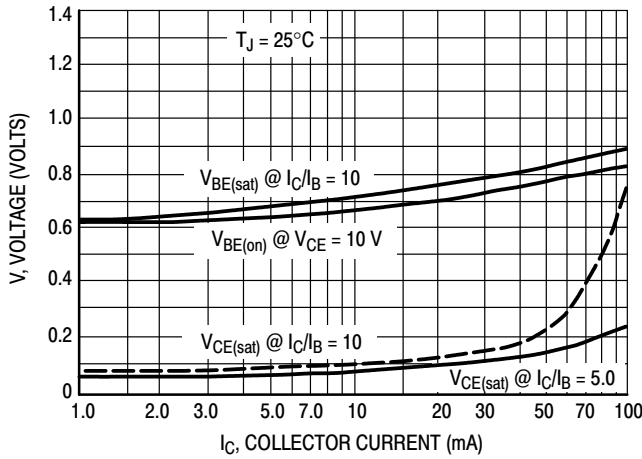


Figure 3. "On" Voltages

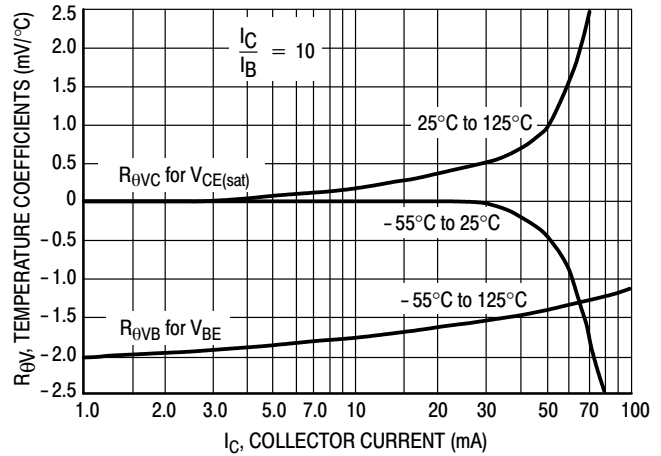


Figure 4. Temperature Coefficients

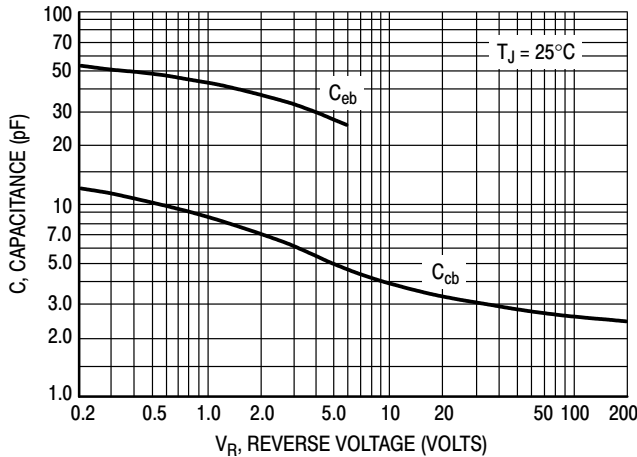


Figure 5. Capacitance

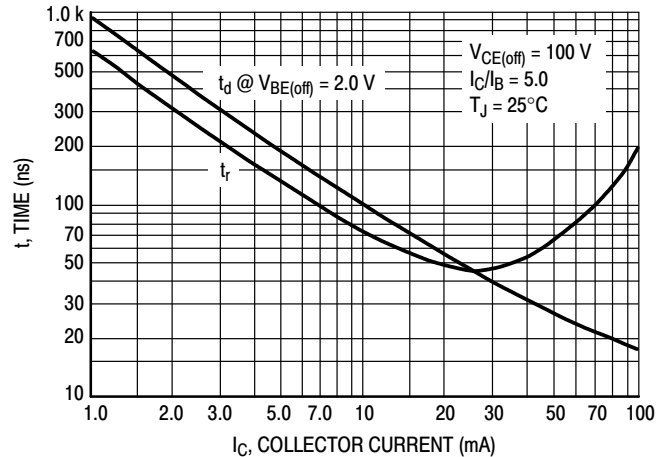


Figure 6. Turn-On Time

MMBT6520L, NSVMMBT6520L

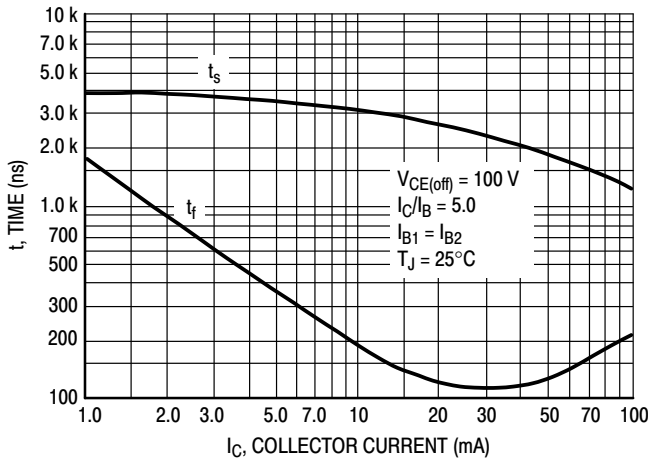


Figure 7. Turn-Off Time

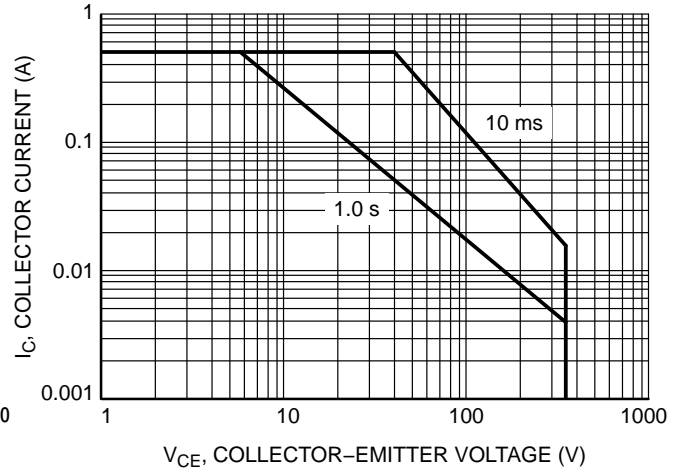


Figure 8. Safe Operating Area

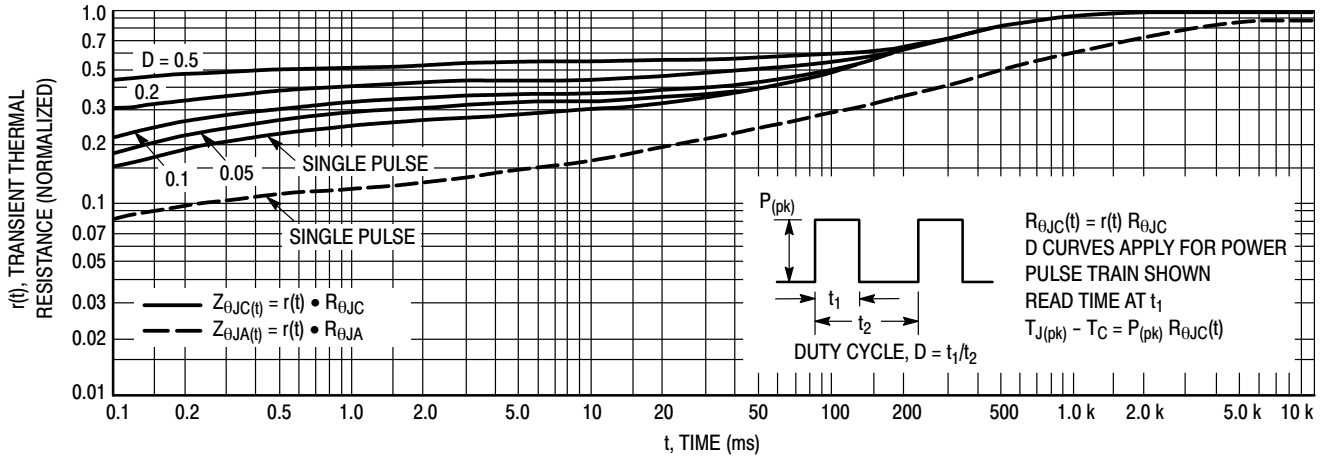


Figure 9. Thermal Response

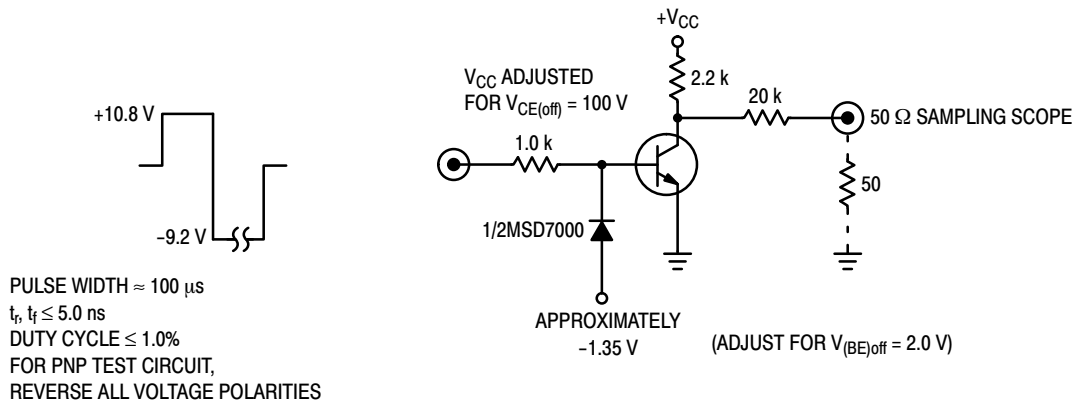


Figure 10. Switching Time Test Circuit

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SOT-23 (TO-236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

SCALE 4:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H _E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

GENERIC MARKING DIAGRAM*



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**



**SOT-23 (TO-236)
CASE 318
ISSUE AT**

DATE 01 MAR 2023

- | | | | | | |
|---|---|---|---|---|---|
| STYLE 1 THRU 5:
CANCELLED | STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR | STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE | | |
| STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE | STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE | STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE | STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE | STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE | STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE |
| STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE | STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE | STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE | STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE | STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE | STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE |
| STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN | STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT | STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE | STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE | STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE | STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION |
| STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE | STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE | | | | |

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